## **SPECIFICATION AMENDMENTS:**

Please substitute the following amended paragraph for paragraph [0007]:

of the photo-resist layer 140 will undulate. After that, another photo-resist layer 145 will be formed on the photo-resist layer 140, meanwhile, a via hole 148 will be formed through the manufacturing process of photolithography and etching, such that part of the drain 130 will be exposed.

Please substitute the following amended paragraph for paragraph [0023]:

[0023] Last, as shown in FIG. 2F, the protection layer 230 will be covered with a transparent electrode 230-235 composed of indium-tin oxide (ITO), wherein the transparent electrode makes the drain 220 and the photo-reflective layer 225 become electrically connected via the first opening 230A and the second opening 230B.

Please substitute the following amended paragraph for paragraph [0024]:

[0024] In the present embodiment, the photo-resist block 210 is situated exactly on the capacitor electrode 204 while the photo-reflective layer 225 is largely substantially formed above the capacitor electrode 204, giving a maximum aperture ration for the TFT-LCD panel according to the invention. It is to be understood that the invention is not to be limited to the above layout: the photo-reflective layer 225 can also be formed at somewhere else but the source 215 and the drain 220.

Please substitute the following amended paragraph for paragraph [0025]:

[0025] Please refer to FIG. 2F again. The transflective TFT-LCD panel formed through the manufacturing method according to the invention has a transmissive area R1 and a reflective area R2. The gate 202, the channel 208, the source 215 and the drain 220 together form a thin film transistor 240. The transparent electrode 235 is formed within the transmissive area R1 and is electrically connected to the drain 220. The photo-reflective layer 225, located within the reflective area R2, is electrically connected to the transparent electrode 235 and the drain 220 by the transparent electrode 235.